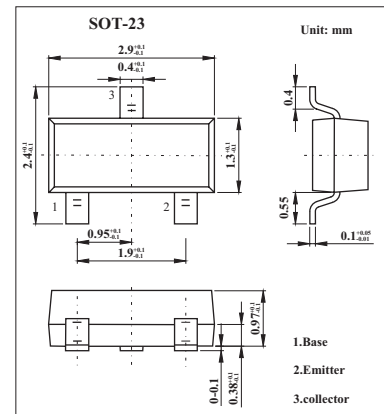


## Silicon PNP Epitaxial

## 2SA1468

## ■ Features

- High voltage amplifier.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	-180	V
Collector to emitter voltage	$V_{CEO}$	-180	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-180			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.5 \text{ mA}, R_{BE} = \infty$	-180			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
DC current transfer ratio	$h_{FE}$	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$	100		320	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -30 \text{ mA}, I_B = -3 \text{ mA}$			-0.5	V
Base emitter voltage	$V_{BE}$	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$			-1	V
Gain bandwidth product	$f_T$	$V_{CE} = -12 \text{ V}, I_C = -10 \text{ mA}$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3.5		pF

## ■ hFE Classification

Marking	INB	INC
Rank	B	C
hFE	100~200	160~320